## B.E. Electronics & Telecommunication / Communication Engineering / Electronics Engineering Eighth Semester

## EC / EN8052 - Elective-II : Micro Electro Mechanical Systems

<ul> <li>Notes : 1. All questions carry marks as indicated.</li> <li>2. Due credit will be given to neatness and adequate dimensions.</li> <li>3. Assume suitable data wherever necessary.</li> <li>4. Illustrate your answers wherever necessary with the help of neat sketches.</li> <li>a) Explain the various sensor characteristics that has to be considered while developing a sensor.</li> <li>b) Compare the various actuation methods used for MEMS devices and also give the general criteria when considering actuators designs and selection.</li> <li>OR</li> <li>2. a) Discuss about the frequently used microfabrication processes.</li> <li>b) A cylindrical silicon rod is pulled on both ends with a force of 10 mN. The rod is 1mm long and 100 - µm in diameter. Find the stress and strain in the longitudinal direction of the rod.</li> <li>c) Give the methods for analyzing the deflection of beams under simple loading conditions.</li> <li>3. a) Explain pull in effect of parallel plate actuators.</li> <li>b) Discuss the procedures for calculating the equilibrium displacement under static (DC) and quasistatic (low frequency) bias conditions of electrostatic actuator under bias.</li> <li>OR</li> <li>4. a) Why must thermal couples involve two different materials ? Explain.</li> <li>b) Write a short note on thermal resistors.</li> <li>5. a) A fixed-free cantilever is made of single crystal silicon. The longitudinal axis of the cantilever points in the [100] crystal orientation. The resistor is made of by diffusion doping, with a longitudinal gauge factor of 50. The length (<i>b</i>, width (w), and thickness (t) of the cantilever are 200 µm, 20 µm and 5 µm, respectively. If a force F = 100 µN is applied at the end of the cantilever in the longitudinal direction, what would be the percentage change of resistance.</li> </ul>	P. Pages : 2 Time : Three Hours			Irs * 1 5 5 1 *	GUG/W/18/2033 Max. Marks : 8	
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OR				OR		

6.	a)	Give the mathematical description of Piegoelectric effect.	
	b)	Explain a compact model for calculating the curvature of bending in a cantilever piezoelectric actuator.	8
7.	a)	Explain the process of low-pressure chemical vapour deposition with diagrams.	8
	b)	Give the material selection criteria for two layer process.	8
		OR	
8.	a)	Give the practical factors affecting the yield of MEMS.	8
	b)	Write a short note on stiction and anti stiction methods. Suggest ways to reduce stiction.	8
9.	a)	Explain the role of SU-8 polymer for MEMS applications.	8
	b)	Write a short note on Parylene as a polymer for MEMS devices.	8
		OR	
10.	a)	Explain the working of multimodal polymer based tactile sensor.	8
	b)	Draw the schematic diagram of a LCP polymer flow sensor and explain the working.	8

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